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ABSTRACT

ading plate has self-stopping capability such that when an object, \$\forall \text{uch as a semiconductor wafer having a} device structure that includes raised regions and depressed regions fabricated ϕ n the surface, is being polished, the regions are removed and polishing raised automatically. The abrading plate, to produce a flat and mirror polished sunface on an object, has abrasive particles having a chemical purity of not less than 90 % and a particle size of I not more than two micrometers, a binder material, and a ϕ iven volume of porosity. A ratio of the abrasive particles and the binder material is not less than 1:0.5 by volume/ and proportions of abrasive particles, a binder material and porosity are, respectively, not less than 10 %, nok more than 60 % and 10~40 by volume. A surface is polished for a given duration with a liquid not containing ab dasive particles so as to eliminate the raised regions to ϕ btain a flat surface. Additional surface removal is performed by supplying abrasive particles to the polishing interface to remove surface material uniformly from the entire surface.